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I hereby certify that this correspondence is being deposited on 1/22/07 with the United States Postal Service with sufficient postage as first class mail under 37 CFR 1.8 in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date 1/22/07

Signature: Joanne Ryan

Joanne Ryan

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

APPLICANT(S) : Richard A. Blanchard et al.

PATENT NO. : 7,019,360 B2

ISSUED : March 28, 2006

TITLE : HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS FORMED BY TRENCH ETCHING USING AN ETCHANT GAS THAT IS ALSO A DOPING SOURCE

DOCKET : GS 174 D1

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

REQUEST FOR CERTIFICATE OF CORRECTION

Applicant's attorney, on behalf of the Assignee of record, hereby requests the issuance of a Certificate of Correction for the following Applicant errors pursuant to 35 USC §255:

Correction is requested for the following Applicant mistakes:

Col. 3, line 66, after "conductivity", add --type--.

Col. 5, line 7, after "silicon", first occurrence, change "ioxide" to --dioxide--.

Certificate

JAN 31 2007

of Correction

FEB 1 2007

U.S. Patent 7,019,360

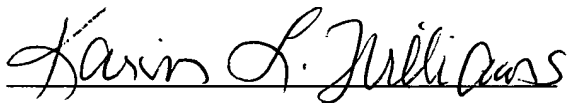
Col. 5, lines 34-35, after "sus-taining", change "regions" to --region--.

Col. 5, line 45, after "The", change "polysilcon" to --polysilicon--.

The PTO is hereby authorized to charge the undersigned attorney's PTO deposit account #50-1047 accordingly.

A PTO-1050 is enclosed; a Certificate of Correction is respectfully requested.

Respectfully submitted:



Date: 1/17/07

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FEB 1 2007

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO : 7,019,360 B2

DATED : March 28, 2006

INVENTOR(S): Richard A. Blanchard et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 3, line 66, after "conductivity", add --type--.

Col. 5, line 7, after "silicon", first occurrence, change "ioxide" to --dioxide--.

Col. 5, lines 34-35, after "sus-taining", change "regions" to --region--.

Col. 5, line 45, after "The", change "polysilcon" to --polysilicon--.

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PATENT NO.

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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete the form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1350.

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